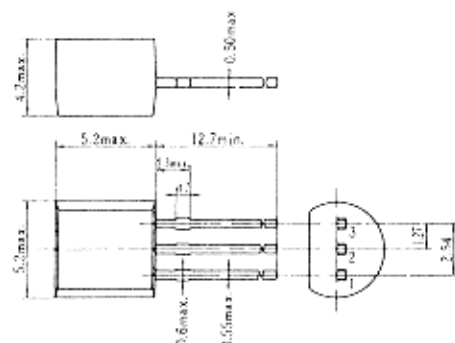


2SC1515 (K)

SILICON NPN TRIPLE DIFFUSED
HIGH VOLTAGE SWITCHING



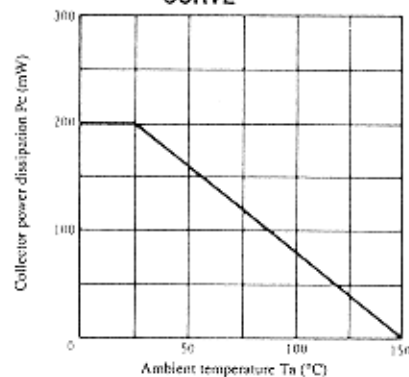
1. Emitter
 2. Collector
 3. Base
- (Dimensions in mm)

(JEDEC TO-92)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC1515 (K)	Unit
Collector to base voltage	V _{CB0}	200	V
Collector to emitter voltage	V _{CES}	200	V
Collector to emitter voltage	V _{CEO}	150	V
Emitter to base voltage	V _{EB0}	5	V
Collector current	I _C	50	mA
Collector power dissipation	P _C	200	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

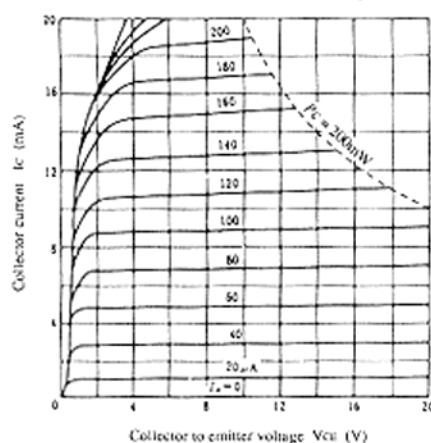
MAXIMUM COLLECTOR DISSIPATION CURVE



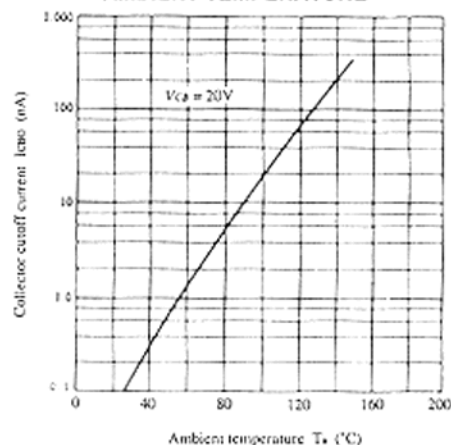
■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to emitter breakdown voltage	V _{(BR)CES}	I _C = 10μA, R _{BE} = 0	200	—	—	V
	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	150	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = 10μA, I _C = 0	5	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = 20V, I _E = 0	—	—	0.1	μA
DC current transfer ratio	h _{FE}	V _{CE} = 6V, I _C = 10mA	30	—	300	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 10mA, I _B = 1mA	—	—	1.0	V
Base to emitter saturation voltage	V _{BE(sat)}	I _C = 10mA, I _B = 1mA	—	—	1.5	V
Gain bandwidth product	f _T	V _{CE} = 6V, I _C = 10mA	60	—	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = 6V, I _E = 0, f = 1MHz	—	—	10	pF

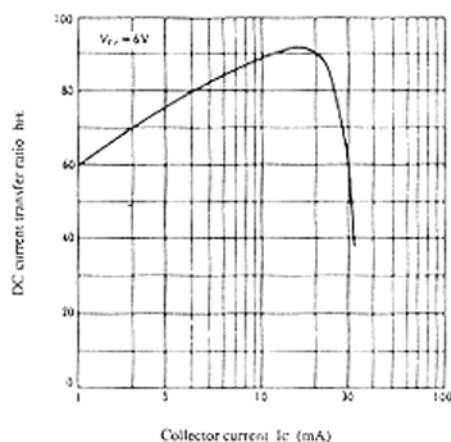
TYPICAL OUTPUT CHARACTERISTICS



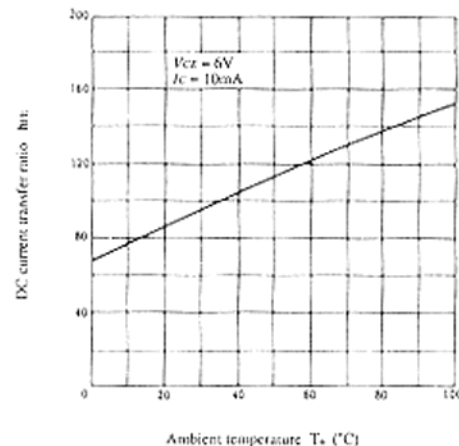
COLLECTOR CUTOFF CURRENT VS. AMBIENT TEMPERATURE



DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



DC CURRENT TRANSFER RATIO VS. AMBIENT TEMPERATURE



COLLECTOR TO EMITTER SATURATION VOLTAGE VS. COLLECTOR CURRENT

